

NTZD3154N

Small Signal MOSFET

20 V, 540 mA, Dual N-Channel

Features

- Low $R_{DS(on)}$ Improving System Efficiency
- Low Threshold Voltage
- Small Footprint 1.6 x 1.6 mm
- ESD Protected Gate
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Management
- Cell Phones, Digital Cameras, PDAs, Pagers, etc.

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted.)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	20	V
Gate-to-Source Voltage		V_{GS}	± 7.0	V
Continuous Drain Current (Note 1)	Steady State	I_D	$T_A = 25^\circ\text{C}$ 540	mA
			$T_A = 85^\circ\text{C}$ 390	
Power Dissipation (Note 1)	Steady State	P_D	250	mW
Continuous Drain Current (Note 1)	$t \leq 5 \text{ s}$	I_D	$T_A = 25^\circ\text{C}$ 570	mA
			$T_A = 85^\circ\text{C}$ 410	
Power Dissipation (Note 1)	$t \leq 5 \text{ s}$	P_D	280	mW
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	I_{DM}	1.5	A
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Source Current (Body Diode)		I_S	350	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	500	$^\circ\text{C/W}$
Junction-to-Ambient – $t \leq 5 \text{ s}$ (Note 1)		447	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

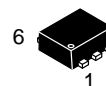
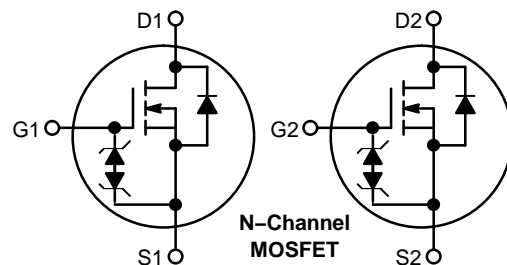
1. Surface mounted on FR4 board using 1 in sq pad size
(Cu. area = 1.127 in sq [1 oz] including traces).



ON Semiconductor®

www.onsemi.com

$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max (Note 1)
20	400 m Ω @ 4.5 V	540 mA
	500 m Ω @ 2.5 V	
	700 m Ω @ 1.8 V	



SOT-563-6
CASE 463A

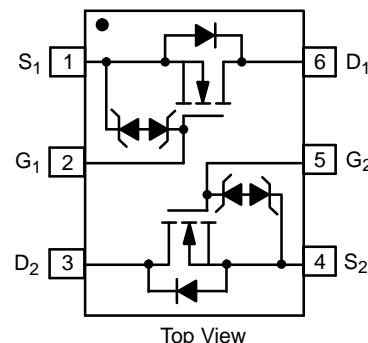
TV = Specific Device Code
M = Date Code
■ = Pb-Free Package

(Note: Microdot may be in either location)

MARKING DIAGRAM



PINOUT: SOT-563



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

NTZD3154N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted.)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
-----------	--------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA		20	–	–	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	–		–	14	–	mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V V _{DS} = 16 V	T _J = 25°C	–	–	1.0	μA
			T _J = 125°C	–	–	5.0	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 4.5 V		–	–	± 5.0	μA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	0.45	–	1.0	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J	–	–	2.0	–	mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 540 mA	–	0.4	0.55	Ω
		V _{GS} = 2.5 V, I _D = 500 mA	–	0.5	0.7	
		V _{GS} = 1.8 V, I _D = 350 mA	–	0.7	0.9	
Forward Transconductance	g _{FS}	V _{DS} = 10 V, I _D = 540 mA	–	1.0	–	S

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 16 V	–	80	150	pF
Output Capacitance	C _{OSS}		–	13	25	
Reverse Transfer Capacitance	C _{RSS}		–	10	20	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 10 V; I _D = 540 mA	–	1.5	2.5	nC
Threshold Gate Charge	Q _{G(TH)}		–	0.1	–	
Gate-to-Source Charge	Q _{GS}		–	0.2	–	
Gate-to-Drain Charge	Q _{GD}		–	0.35	–	

SWITCHING CHARACTERISTICS, V_{GS} = V (Note 4)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DD} = 10 V, I _D = 540 mA, R _G = 10 Ω	–	6.0	–	ns
Rise Time	t _r		–	4.0	–	
Turn-Off Delay Time	t _{d(OFF)}		–	16	–	
Fall Time	t _f		–	8.0	–	

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 350 mA	T _J = 25°C	–	0.7	1.2	V
			T _J = 125°C	–	0.6	–	
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _{SD} /dt = 100 A/μs, I _S = 350 mA	–	6.5	–	–	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Surface-mounted on FR4 board using 1 in. sq. pad size (Cu. area = 1.127 in sq [1 oz] including traces).
- Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

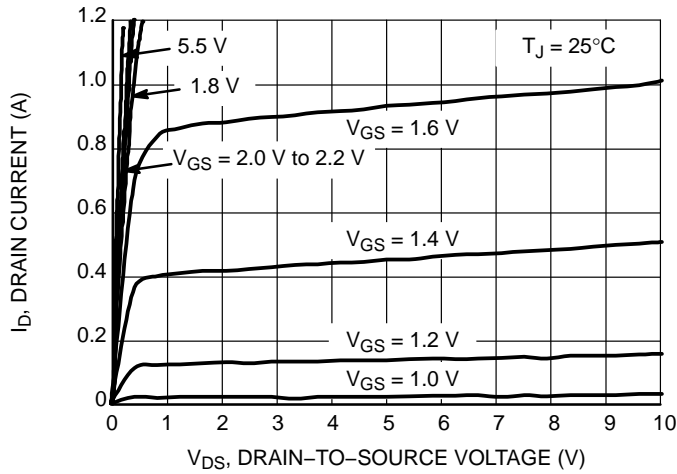


Figure 1. On-Region Characteristics

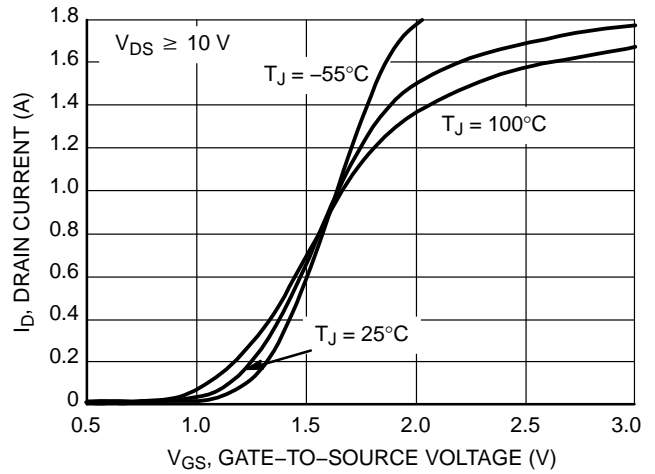


Figure 2. Transfer Characteristics

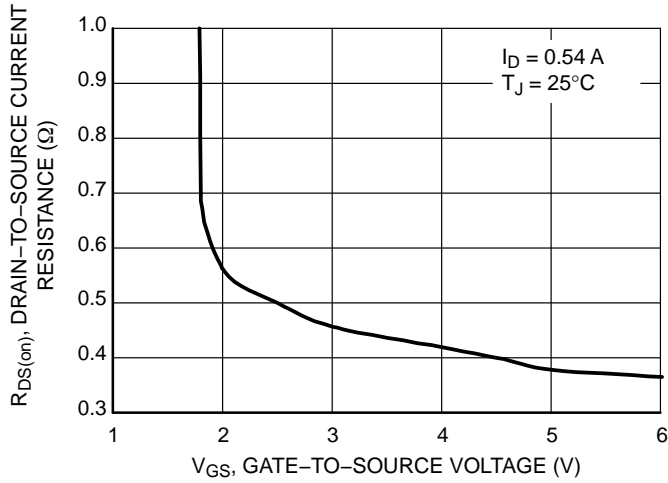


Figure 3. On-Resistance versus Gate-to-Source Voltage

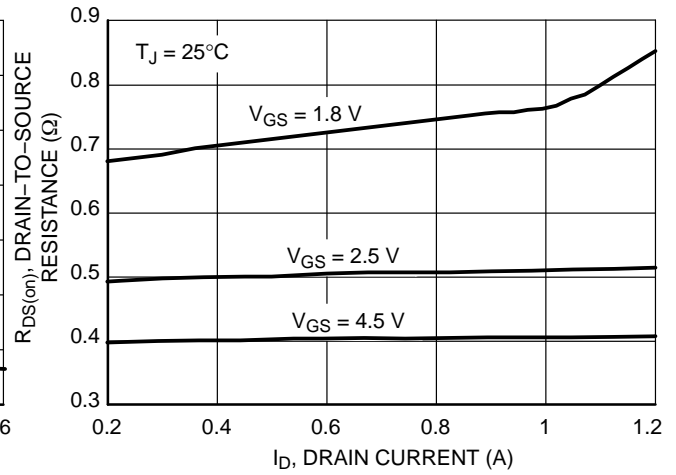


Figure 4. On-Resistance versus Drain Current and Gate Voltage

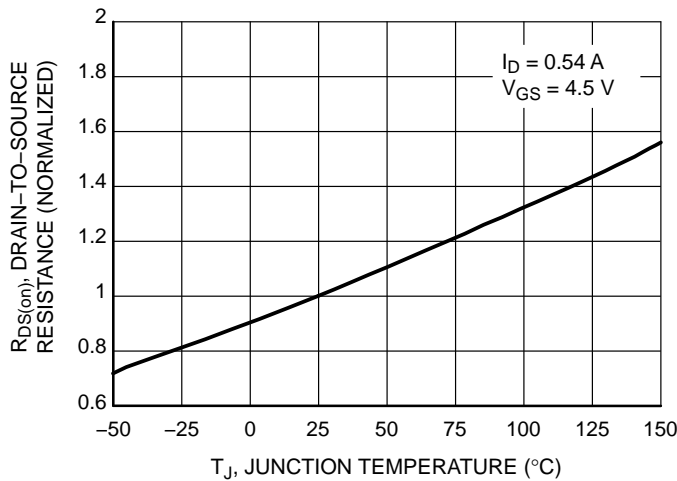


Figure 5. On-Resistance Variation with Temperature

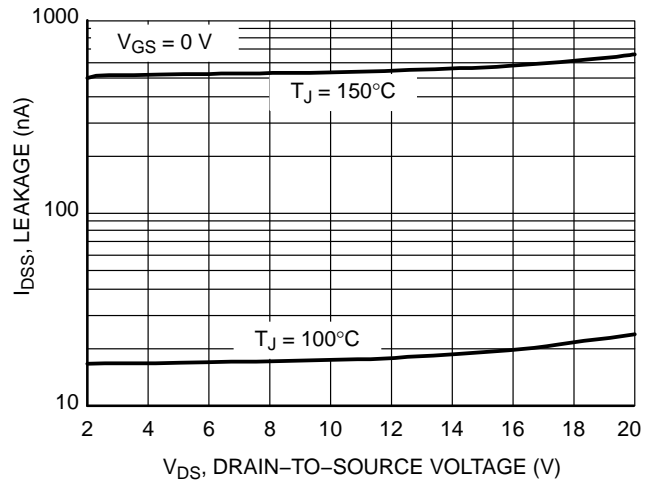
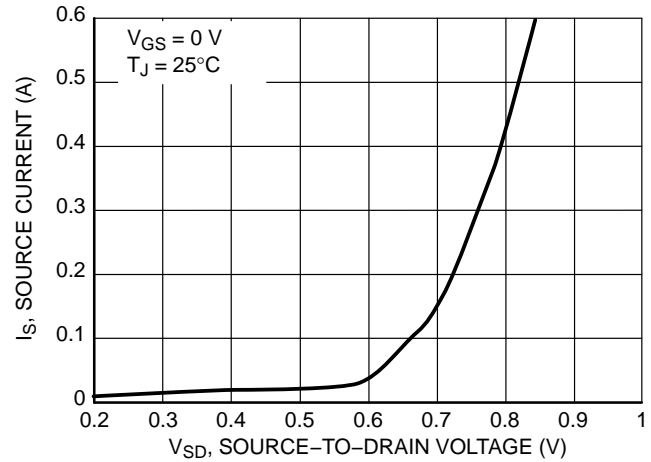
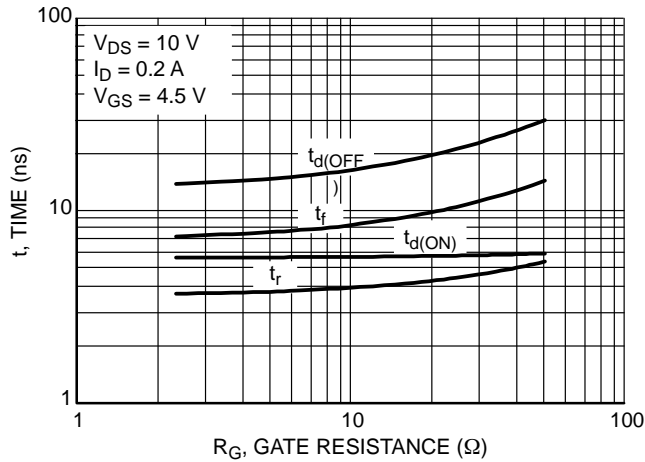
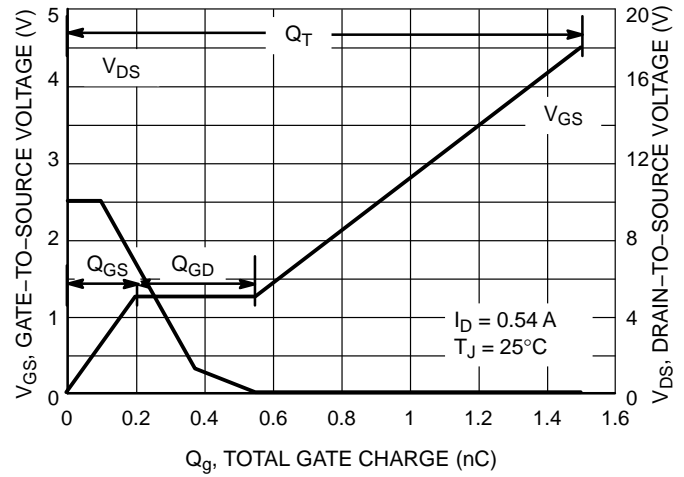
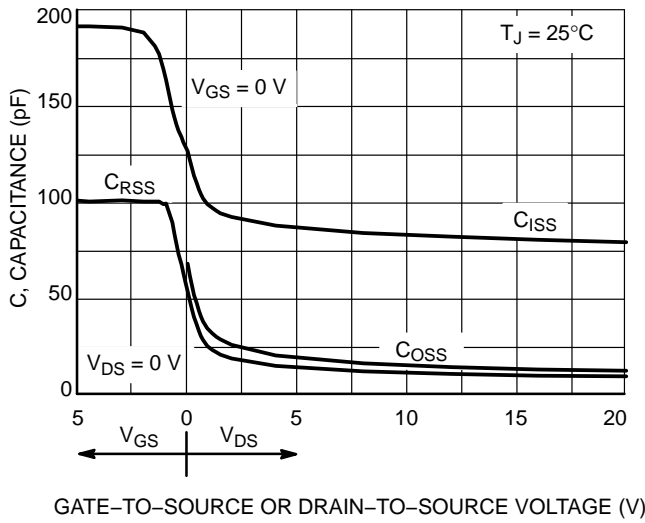


Figure 6. Drain-to-Source Leakage Current versus Voltage

NTZD3154N

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)



ORDERING INFORMATION

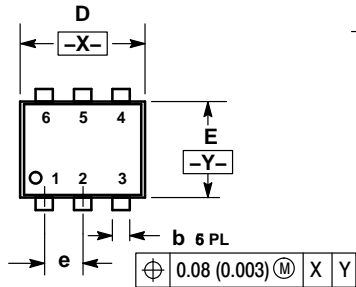
Device	Package	Shipping
NTZD3154NT1G	SOT-563 (Pb-Free)	4000 / Tape & Reel
NTZD3154NT1H		
NTZD3154NT2G		
NTZD3154NT2H		
NTZD3154NT5G		8000 / Tape & Reel
NTZD3154NT5H		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTZD3154N

PACKAGE DIMENSIONS

SOT-563, 6 LEAD CASE 463A ISSUE F

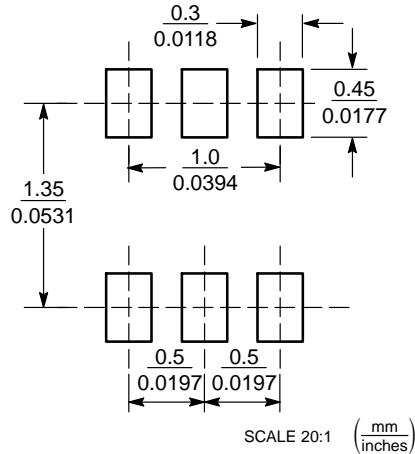


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
C	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
E	1.10	1.20	1.30	0.043	0.047	0.051
e	0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H _E	1.50	1.60	1.70	0.059	0.062	0.066

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative